Welcome to E-XFL.COM

Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 256K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu5cg-l1fbvb900i

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{CCO_PSDDR}	PS DDR I/O supply voltage.	–0.500	1.650	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	–0.500	2.000	V
V_{CCO_PSIO}	PS I/O supply.	–0.500	3.630	V
V_{PSIN}[2]	PS I/O input voltage.	–0.500	V_{CCO_PSIO} + 0.550	V
	PS DDR I/O input voltage.	–0.500	V_{CCO_PSDDR} + 0.550	V
V_{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	–0.500	2.000	V
Programmable Logic (PL)				
V_{CCINT}	Internal supply voltage.	–0.500	1.000	V
V_{CCINT_IO}[3]	Internal supply voltage for the I/O banks.	–0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	–0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	–0.500	1.000	V
V_{CCO}	Output drivers supply voltage for HD I/O banks.	–0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	–0.500	2.000	V
V_{CCAUX_IO}[4]	Auxiliary supply voltage for the I/O banks.	–0.500	2.000	V
V_{REF}	Input reference voltage.	–0.500	2.000	V
V_{IN}[2][5][7]	I/O input voltage for HD I/O banks.[6]	–0.550	V_{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	–0.550	V_{CCO} + 0.550	V
I_{DC}	Available output current at the pad.	–20	20	mA
I_{RMS}	Available RMS output current at the pad.	–20	20	mA
GTH or GTY Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	–0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	–0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	–0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	–0.500	1.300	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	–0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	–0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating.[8]	–	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	–	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND.[9]	–	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable.[10]	–	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	–	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	–	6	mA

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.[12]	–	260	°C
T_j	Maximum junction temperature.[12]	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Table 2: **Recommended Operating Conditions[1][2]** ***(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
V_{CCO}[8]	Supply voltage for HD I/O banks.	1.140	–	3.400	V
	Supply voltage for HP I/O banks.	0.950	–	1.900	V
V_{CCAUX_IO}[9]	Auxiliary I/O supply voltage.	1.746	1.800	1.854	V
V_{IN}[10]	I/O input voltage.	–0.200	–	V_{CCO} + 0.200	V
I_{IN}[11]	Maximum current through any PL or PS pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
GTH or GTY Transceiver					
$V_{MGTAVCC}$[12]	Analog supply voltage for the GTH or GTY transceiver.	0.873	0.900	0.927	V
$V_{MGTAVTT}$[12]	Analog supply voltage for the GTH or GTY transmitter and receiver termination circuits.	1.164	1.200	1.236	V
$V_{MGTVCCAUX}$[12]	Auxiliary analog QPLL voltage supply for the transceivers.	1.746	1.800	1.854	V
$V_{MGTAVTTRCAL}$[12]	Analog supply voltage for the resistor calibration circuit of the GTH or GTY transceiver column.	1.164	1.200	1.236	V
VCU					
V_{CCINT_VCU}	Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -3E devices: Internal supply voltage for the VCU.	0.873	0.900	0.927	V

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[(1)]	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

Table 9: **Typical Quiescent Supply Current[1][2][3][4]** ***(Cont'd)***

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current.	XCZU2	N/A	26	26	26	26	mA
		XCZU3	N/A	26	26	26	26	mA
		XCZU4	32	32	32	32	32	mA
		XCZU5	32	32	32	32	32	mA
		XCZU6	33	33	33	33	33	mA
		XCZU7	56	56	56	56	56	mA
		XCZU9	33	33	33	33	33	mA
		XCZU11	56	56	56	56	56	mA
		XCZU15	33	33	33	33	33	mA
		XCZU17	74	74	74	74	74	mA
		XCZU19	74	74	74	74	74	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XCZU2	N/A	6	6	6	6	mA
		XCZU3	N/A	6	6	6	6	mA
		XCZU4	9	9	9	9	9	mA
		XCZU5	9	9	9	9	9	mA
		XCZU6	25	24	24	24	24	mA
		XCZU7	16	15	15	15	15	mA
		XCZU9	25	24	24	24	24	mA
		XCZU11	23	22	22	22	22	mA
		XCZU15	29	28	28	28	28	mA
		XCZU17	37	35	35	35	35	mA
		XCZU19	37	35	35	35	35	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate static power consumption for conditions or supplies other than those specified.
4. Typical values depend upon your configuration. To accurately estimate all PS supply currents, use the interactive XPE spreadsheet tool.

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: **Power-on Current by Device**(1)

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ} +	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
I_{CCINT_IOMIN} + $I_{CCBRAMMIN}$	$I_{CCBRAMQ}$ + I_{CCINT_IOQ} +	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ} +	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}$ + I_{CCAUX_IOMIN}	I_{CCAUXQ} + I_{CCAUX_IOQ} +	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: **Power Supply Ramp Time**

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT}.	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO}.	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU}.	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO}.	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX}.	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM}.	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC\_PSINTFP}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP}$.	0.2	40	ms
$T_{VCC\_PSINTLP}$	Ramp time from GND to 95% of $V_{CC\_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX}.	0.2	40	ms
$T_{VCC\_PSINTFP\_DDR}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP\_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC}.	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL}.	0.2	40	ms
$T_{PS\_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVCC}$.	0.2	40	ms
$T_{PS\_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVTT}$.	0.2	40	ms

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU11EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU15EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU17EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU19EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Notes:

1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

PS Gigabit Ethernet Controller Interface

Table 44: **RGMII Interface**[1]

Symbol	Description	Min	Max	Units
$T_{DCGEMTXCLK}$	Transmit clock duty cycle.	45	55	%
$T_{GEMTXCKO}$	TXD output clock to out time.	–0.5	0.5	ns
$T_{GEMRXDCK}$	RXD input setup time.	0.8	–	ns
$T_{GEMRXCKD}$	RXD input hold time.	0.8	–	ns
$T_{MDIOCLK}$	MDC output clock period.	400	–	ns
$T_{MDIOCKL}$	MDC low time.	160	–	ns
$T_{MDIOCKH}$	MDC high time.	160	–	ns
$T_{MDIODCK}$	MDIO input data setup time.	80	–	ns
$T_{MDIOCKD}$	MDIO input data hold time.	0.0	–	ns
$T_{MDIOCKO}$	MDIO output data delay time.	–1.0	15	ns
$F_{GETXCLK}$	RGMII_TX_CLK transmit clock frequency.	–	125	MHz
$F_{GERXCLK}$	RGMII_RX_CLK receive clock frequency.	–	125	MHz
$F_{ENET\_REF\_CLK}$	Ethernet reference clock frequency.	–	125	MHz

Notes:

1. The test conditions are configured to the LVCMOS 2.5V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS SD/SDIO Controller Interface

Table 45: **SD/SDIO Interface**[1]

Symbol	Description	Min	Max	Units
SD/SDIO Interface DDR50 Mode				
$T_{DCDDRCLK}$	SD device clock duty cycle.	45	55	%
$T_{SDDDRCKO1}$	Clock to output delay, data.[2]	1.0	6.8	ns
$T_{SDDRIVW}$	Input valid data window.[3]	3.5	–	ns
$T_{SDDDRDCK2}$	Input setup time, command.	4.7	–	ns
$T_{SDDDRCKD2}$	Input hold time, command.	1.5	–	ns
$T_{SDDDRCKO2}$	Clock to output delay, command.	1.0	13.8	ns
$F_{SDDDRCLK}$	High-speed mode SD device clock frequency.	–	50	MHz
SD/SDIO Interface SDR104				
$T_{DCSDHSCLK1}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO1}$	Clock to output delay, all outputs.[2]	1.0	3.2	ns
$T_{SDSDR1IVW}$	Input valid data window.[3]	0.5	–	UI
$F_{SDSDRCLK1}$	SDR104 mode device clock frequency.	–	200	MHz
SD/SDIO Interface SDR50/25				
$T_{DCSDHSCLK2}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO2}$	Clock to output delay, all outputs.[2]	1.0	6.8	ns
$T_{SDSDR2IVW}$	Input valid data window.[3]	0.3	–	UI

Table 45: **SD/SDIO Interface[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
$F_{SDSDRCLK2}$	SDR50 mode device clock frequency.	–	100	MHz
	SDR25 mode device clock frequency.	–	50	MHz
SD/SDIO Interface SDR12				
$T_{DCSDHSCLK3}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO3}$	Clock to output delay, all outputs.	1.0	36.8	ns
$T_{SDSDRDCK3}$	Input setup time, all inputs.	24.0	–	ns
$T_{SDSDRCKD3}$	Input hold time, all inputs.	1.5	–	ns
$F_{SDSDRCLK3}$	SDR12 mode device clock frequency.	–	25	MHz
SD/SDIO Interface High-Speed Mode				
$T_{DCSDHSCLK}$	SD device clock duty cycle.	47	53	%
$T_{SDHSCKO}$	Clock to output delay, all outputs.[2]	2.2	13.8	ns
$T_{SDHSDIVW}$	Input valid data window.[3]	0.35	–	UI
$F_{SDHSCLK}$	High-speed mode SD device clock frequency.	–	50	MHz
SD/SDIO Interface Standard Mode				
$T_{DCSDSCLK}$	SD device clock duty cycle.	45	55	%
T_{SDSCKO}	Clock to output delay, all outputs.	–2.0	4.5	ns
T_{SDSDCK}	Input setup time, all inputs.	2.0	–	ns
T_{SDSCKD}	Input hold time, all inputs.	2.0	–	ns
$F_{SDIDCLK}$	Clock frequency in identification mode.	–	400	KHz
F_{SDSCLK}	Standard SD device clock frequency.	–	19	MHz

Notes:

1. The test conditions SD/SDIO standard mode (default speed mode) use an 8 mA drive strength, fast slew rate, and a 30 pF load. For SD/SDIO high-speed mode, the test conditions use a 12 mA drive strength, fast slew rate, and a 30 pF load. For other SD/SDIO modes, the test conditions use a 12 mA drive strength, fast slew rate, and a 15 pF load.
2. This specification is achieved using pre-determined DLL tuning.
3. This specification is required for capturing input data using DLL tuning.

Programmable Logic (PL) Switching Characteristics

Table 75 (high-density IOB (HD)) and Table 76 (high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF\_DELAY\_PAD\_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- $T_{OUTBUF\_DELAY\_O\_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- $T_{OUTBUF\_DELAY\_TD\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the on-die termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the INTERMDISABLE pin is used.

IOB High Density (HD) Switching Characteristics

Table 75: **IOB High Density (HD) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_18_F	0.978	0.978	1.058	0.978	1.058	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
DIFF_HSTL_I_18_S	0.978	0.978	1.058	0.978	1.058	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns
DIFF_HSTL_I_F	0.978	0.978	1.058	0.978	1.058	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
DIFF_HSTL_I_S	0.978	0.978	1.058	0.978	1.058	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
DIFF_HSUL_12_F	0.911	0.911	0.977	0.911	0.977	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
DIFF_HSUL_12_S	0.911	0.911	0.977	0.911	0.977	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
DIFF_SSTL12_F	0.906	0.906	0.977	0.906	0.977	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
DIFF_SSTL12_S	0.906	0.906	0.977	0.906	0.977	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
DIFF_SSTL135_F	0.927	0.927	0.995	0.927	0.995	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
DIFF_SSTL135_II_F	0.927	0.927	0.995	0.927	0.995	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
DIFF_SSTL135_II_S	0.927	0.927	0.995	0.927	0.995	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
DIFF_SSTL135_S	0.927	0.927	0.995	0.927	0.995	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
DIFF_SSTL15_F	0.928	0.928	1.020	0.928	1.020	1.628	1.628	1.771	1.628	1.771	1.374	1.374	1.483	1.374	1.483	ns
DIFF_SSTL15_II_F	0.928	0.928	1.020	0.928	1.020	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
DIFF_SSTL15_II_S	0.928	0.928	1.020	0.928	1.020	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
DIFF_SSTL15_S	0.928	0.928	1.020	0.928	1.020	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
DIFF_SSTL18_II_F	0.961	0.961	1.038	0.961	1.038	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
DIFF_SSTL18_II_S	0.961	0.961	1.038	0.961	1.038	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
DIFF_SSTL18_I_F	0.961	0.961	1.038	0.961	1.038	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
DIFF_SSTL18_I_S	0.961	0.961	1.038	0.961	1.038	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
HSTL_I_18_F	0.947	0.947	1.021	0.947	1.021	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
HSTL_I_18_S	0.947	0.947	1.021	0.947	1.021	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
LVCMOS33_S_8	1.154	1.154	1.213	1.154	1.213	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
LVDS_25	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVTTL_F_12	1.164	1.164	1.223	1.164	1.223	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVTTL_F_16	1.164	1.164	1.223	1.164	1.223	2.464	2.464	2.732	2.464	2.732	1.750	1.750	1.986	1.750	1.986	ns
LVTTL_F_4	1.164	1.164	1.223	1.164	1.223	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVTTL_F_8	1.164	1.164	1.223	1.164	1.223	2.582	2.582	2.787	2.582	2.787	1.910	1.910	2.063	1.910	2.063	ns
LVTTL_S_12	1.164	1.164	1.223	1.164	1.223	2.731	2.731	3.075	2.731	3.075	2.072	2.072	2.343	2.072	2.343	ns
LVTTL_S_16	1.164	1.164	1.223	1.164	1.223	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVTTL_S_4	1.164	1.164	1.223	1.164	1.223	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns
LVTTL_S_8	1.164	1.164	1.223	1.164	1.223	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
SLVS_400_25	1.020	1.020	1.136	1.020	1.136	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_F	0.780	0.780	0.867	0.780	0.867	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
SSTL12_S	0.780	0.780	0.867	0.780	0.867	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
SSTL135_F	0.798	0.798	0.881	0.798	0.881	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
SSTL135_II_F	0.798	0.798	0.881	0.798	0.881	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
SSTL135_II_S	0.798	0.798	0.881	0.798	0.881	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
SSTL135_S	0.798	0.798	0.881	0.798	0.881	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
SSTL15_F	0.838	0.838	0.880	0.838	0.880	1.612	1.612	1.754	1.612	1.754	1.357	1.357	1.464	1.357	1.464	ns
SSTL15_II_F	0.838	0.838	0.880	0.838	0.880	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
SSTL15_II_S	0.838	0.838	0.880	0.838	0.880	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
SSTL15_S	0.838	0.838	0.880	0.838	0.880	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
SSTL18_II_F	0.947	0.947	1.021	0.947	1.021	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
SSTL18_II_S	0.947	0.947	1.021	0.947	1.021	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
SSTL18_I_F	0.947	0.947	1.021	0.947	1.021	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
SSTL18_I_S	0.947	0.947	1.021	0.947	1.021	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
SUB_LVDS	1.002	1.002	1.036	1.002	1.036	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns

Input Delay Measurement Methodology

Table 78 shows the test setup parameters used for measuring input delay.

Table 78: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
LVCMOS, 1.2V	LVCMOS12	0.1	1.1	0.6	–
LVCMOS, LVDCI, HSLVDCI, 1.5V	LVCMOS15, LVDCI_15, HSLVDCI_15	0.1	1.4	0.75	–
LVCMOS, LVDCI, HSLVDCI, 1.8V	LVCMOS18, LVDCI_18, HSLVDCI_18	0.1	1.7	0.9	–
LVCMOS, 2.5V	LVCMOS25	0.1	2.4	1.25	–
LVCMOS, 3.3V	LVCMOS33	0.1	3.2	1.65	–
LVTTL, 3.3V	LVTTL	0.1	3.2	1.65	–
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	V_{REF} – 0.2875	V_{REF} + 0.2875	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
SSTL18, class I and II, 1.8V	SSTL18_I, SSTL18_II	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
POD10, 1.0V	POD10	V_{REF} – 0.2	V_{REF} + 0.2	V_{REF}	0.7
POD12, 1.2V	POD12	V_{REF} – 0.24	V_{REF} + 0.24	V_{REF}	0.84
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_HSUL, 1.2V	DIFF_HSUL_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL, 1.2V	DIFF_SSTL12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	0.675 – 0.2875	0.675 + 0.2875	0(6)	–
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_SSTL18_I, DIFF_SSTL18_II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_POD10, 1.0V	DIFF_POD10	0.5 – 0.2	0.5 + 0.2	0(6)	–
DIFF_POD12, 1.2V	DIFF_POD12	0.6 – 0.25	0.6 + 0.25	0(6)	–
LVDS (low-voltage differential signaling), 1.8V	LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
LVDS_25, 2.5V	LVDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–

Block RAM and FIFO Switching Characteristics

Table 80: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
$F_{MAX\_WF\_NC}$	Block RAM (WRITE_FIRST and NO_CHANGE modes).	825	738	645	585	516	MHz
F_{MAX_RF}	Block RAM (READ_FIRST mode).	718	637	575	510	460	MHz
F_{MAX_FIFO}	FIFO in all modes without ECC.	825	738	645	585	516	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration without PIPELINE.	718	637	575	510	460	MHz
	Block RAM and FIFO in ECC configuration with PIPELINE and Block RAM in WRITE_FIRST or NO_CHANGE mode.	825	738	645	585	516	MHz
T_{PW}[(1)]	Minimum pulse width.	495	542	543	577	578	ps
Block RAM and FIFO Clock-to-Out Delays							
T_{RCKO_DO}	Clock CLK to DOUT output (without output register).	0.91	1.02	1.11	1.46	1.53	ns, Max
$T_{RCKO\_DO\_REG}$	Clock CLK to DOUT output (with output register).	0.27	0.29	0.30	0.42	0.44	ns, Max

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

MMCM Switching Characteristics

Table 85: **MMCM Specification**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$MMCM\_F_{INMAX}$	Maximum input clock frequency.	1066	933	800	933	800	MHz
$MMCM\_F_{INMIN}$	Minimum input clock frequency.	10	10	10	10	10	MHz
$MMCM\_F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max					
$MMCM\_F_{INDUTY}$	Input duty cycle range: 10–49 MHz.	25–75					%
	Input duty cycle range: 50–199 MHz.	30–70					%
	Input duty cycle range: 200–399 MHz.	35–65					%
	Input duty cycle range: 400–499 MHz.	40–60					%
	Input duty cycle range: >500 MHz.	45–55					%
$MMCM\_F_{MIN\_PSCLK}$	Minimum dynamic phase shift clock frequency.	0.01	0.01	0.01	0.01	0.01	MHz
$MMCM\_F_{MAX\_PSCLK}$	Maximum dynamic phase shift clock frequency.	550	500	450	500	450	MHz
$MMCM\_F_{VCOMIN}$	Minimum MMCM VCO frequency.	800	800	800	800	800	MHz
$MMCM\_F_{VCOMAX}$	Maximum MMCM VCO frequency.	1600	1600	1600	1600	1600	MHz
$MMCM\_F_{BANDWIDTH}$	Low MMCM bandwidth at typical.[1]	1.00	1.00	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical.[1]	4.00	4.00	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs.[2]	0.12	0.12	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM output jitter.	Note 3					
$MMCM\_T_{OUTDUTY}$	MMCM output clock duty cycle precision.[4]	0.165	0.20	0.20	0.20	0.20	ns
$MMCM\_T_{LOCKMAX}$	MMCM maximum lock time for $MMCM\_F_{PFDMIN}$.	100	100	100	100	100	µs
$MMCM\_F_{OUTMAX}$	MMCM maximum output frequency.	891	775	667	725	667	MHz
$MMCM\_F_{OUTMIN}$	MMCM minimum output frequency.[4][5]	6.25	6.25	6.25	6.25	6.25	MHz
$MMCM\_T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max					
$MMCM\_RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	5.00	5.00	ns
$MMCM\_F_{PFDMAX}$	Maximum frequency at the phase frequency detector.	550	500	450	500	450	MHz
$MMCM\_F_{PFDMIN}$	Minimum frequency at the phase frequency detector.	10	10	10	10	10	MHz
$MMCM\_T_{FBDELAY}$	Maximum delay in the feedback path.	5 ns Max or one clock cycle					

Table 88: **Global Clock Input to Output Delay Without MMCM (Far Clock Region)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM.								
T_{ICKOF_FAR}	Global clock input and output flip-flop *without* MMCM (far clock region).	XCZU2	N/A	5.27	5.68	5.80	6.13	ns
		XCZU3	N/A	5.27	5.68	5.80	6.13	ns
		XCZU4	5.07	6.06	6.61	6.23	7.10	ns
		XCZU5	5.07	6.06	6.61	6.23	7.10	ns
		XCZU6	5.38	6.49	6.97	7.14	7.59	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.38	6.49	6.97	7.14	7.59	ns
		XCZU11	6.18	7.41	8.11	7.66	8.99	ns
		XCZU15	5.38	6.49	6.96	7.19	7.71	ns
		XCZU17	6.21	7.53	8.07	8.36	8.90	ns
		XCZU19	6.21	7.53	8.07	8.36	8.90	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 89: **Global Clock Input to Output Delay With MMCM**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with MMCM.								
$T_{ICKOFMMCMCC}$	Global clock input and output flip-flop *with* MMCM.	XCZU2	N/A	2.22	2.43	2.96	2.94	ns
		XCZU3	N/A	2.22	2.43	2.96	2.94	ns
		XCZU4	2.47	2.47	2.78	3.04	3.35	ns
		XCZU5	2.47	2.47	2.78	3.04	3.35	ns
		XCZU6	2.15	2.15	2.36	2.86	2.86	ns
		XCZU7	2.32	2.32	2.57	3.06	3.13	ns
		XCZU9	2.15	2.15	2.36	2.86	2.86	ns
		XCZU11	2.64	2.64	2.96	3.25	3.55	ns
		XCZU15	2.18	2.18	2.38	2.88	2.90	ns
		XCZU17	2.44	2.44	2.66	3.19	3.17	ns
		XCZU19	2.44	2.44	2.66	3.19	3.17	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Device Pin-to-Pin Input Parameter Guidelines

The pin-to-pin numbers in Table 90 and Table 91 are based on the clock root placement in the center of the device. The actual pin-to-pin values will vary if the root placement selected is different. Consult the Vivado Design Suite timing report for the actual pin-to-pin values.

Table 90: **Global Clock Input Setup and Hold With 3.3V HD I/O without MMCM**

Symbol	Description	Device		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
				-3	-2	-1	-2	-1	
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.[1][2][3]									
T_{PSFD_ZU2}	Global clock input and input flip-flop (or latch) without MMCM.	Setup	XCZU2	N/A	2.27	2.37	2.55	2.64	ns
T_{PHFD_ZU2}		Hold			–0.36	–0.36	–0.14	–0.14	ns
T_{PSFD_ZU3}		Setup	XCZU3	N/A	2.27	2.37	2.55	2.64	ns
T_{PHFD_ZU3}		Hold			–0.36	–0.36	–0.14	–0.14	ns
T_{PSFD_ZU4}		Setup	XCZU4	1.28	2.01	2.07	2.59	2.59	ns
T_{PHFD_ZU4}		Hold		–0.28	–0.28	–0.28	–0.09	–0.09	ns
T_{PSFD_ZU5}		Setup	XCZU5	1.28	2.01	2.07	2.59	2.59	ns
T_{PHFD_ZU5}		Hold		–0.28	–0.28	–0.28	–0.09	–0.09	ns
T_{PSFD_ZU6}		Setup	XCZU6	0.96	1.79	1.86	1.93	2.02	ns
T_{PHFD_ZU6}		Hold		–0.05	–0.05	–0.05	0.27	0.42	ns
T_{PSFD_ZU7}		Setup	XCZU7	1.43	2.32	2.42	2.60	2.69	ns
T_{PHFD_ZU7}		Hold		–0.40	–0.40	–0.40	–0.21	–0.21	ns
T_{PSFD_ZU9}		Setup	XCZU9	0.96	1.79	1.86	1.93	2.02	ns
T_{PHFD_ZU9}		Hold		–0.05	–0.05	–0.05	0.27	0.42	ns
T_{PSFD_ZU11}		Setup	XCZU11	1.28	2.01	2.07	2.59	2.59	ns
T_{PHFD_ZU11}		Hold		–0.29	–0.29	–0.29	–0.09	0.19	ns
T_{PSFD_ZU15}		Setup	XCZU15	0.96	1.79	1.85	1.92	2.01	ns
T_{PHFD_ZU15}		Hold		–0.04	–0.04	–0.04	0.27	0.43	ns
T_{PSFD_ZU17}		Setup	XCZU17	1.41	2.29	2.38	2.57	2.65	ns
T_{PHFD_ZU17}		Hold		–0.38	–0.38	–0.38	–0.19	–0.19	ns
T_{PSFD_ZU19}		Setup	XCZU19	1.41	2.29	2.38	2.57	2.65	ns
T_{PHFD_ZU19}		Hold		–0.38	–0.38	–0.38	–0.19	–0.19	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Package Parameter Guidelines

The parameters in this section provide the necessary values for calculating timing budgets for clock transmitter and receiver data-valid windows.

Table 93: **Package Skew**

Symbol	Description	Device	Package	Value	Units
PKGSKEW	Package Skew	XCZU2	SBVA484	105	ps
			SFVA625	108	ps
			SFVC784	93	ps
		XCZU3	SBVA484	105	ps
			SFVA625	108	ps
			SFVC784	93	ps
		XCZU4	SFVC784		ps
			FBVB900		ps
		XCZU5	SFVC784		ps
			FBVB900		ps
		XCZU6	FFVC900	119	ps
			FFVB1156	134	ps
		XCZU7	FBVB900	141	ps
			FFVC1156	175	ps
			FFVF1517	305	ps
		XCZU9	FFVC900	119	ps
			FFVB1156	134	ps
		XCZU11	FFVC1156		ps
			FFVB1517		ps
			FFVF1517		ps
			FFVC1760	215	ps
		XCZU15	FFVC900	118	ps
			FFVB1156	132	ps
		XCZU17	FFVB1517	221	ps
			FFVC1760	226	ps
			FFVD1760	178	ps
			FFVE1924	174	ps
		XCZU19	FFVB1517	221	ps
			FFVC1760	226	ps
			FFVD1760	178	ps
			FFVE1924	174	ps

Notes:

1. These values represent the worst-case skew between any two SelectIO resources in the package: shortest delay to longest delay from die pad to ball.
2. Package delay information is available for these device/package combinations. This information can be used to deskew the package.

Table 102: **GTH Transceiver User Clock Switching Characteristics[(1)] *(Cont'd)***

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3[(2)]	-2[(2)(3)]	-1[(4)(5)]	-2[(3)]	-1[(5)]	
$F_{TXOUTPROGDIV}$	TXOUTCLK maximum frequency sourced from TXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
$F_{RXOUTPROGDIV}$	RXOUTCLK maximum frequency sourced from RXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
F_{TXIN}	TXUSRCLK[(6)] maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	312.500	257.813	MHz
F_{RXIN}	RXUSRCLK[(6)] maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	312.500	257.813	MHz
F_{TXIN2}	TXUSRCLK2[(6)] maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	312.500	257.813	MHz
		40	80	204.688	204.688	156.250	156.250	128.906	MHz
F_{RXIN2}	RXUSRCLK2[(6)] maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	312.500	257.813	MHz
		40	80	204.688	204.688	156.250	156.250	128.906	MHz

Notes:

1. Clocking must be implemented as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576).
2. For speed grades -3E, -2E, and -2I, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s.
3. For speed grade -2LE, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s when V_{CCINT} = 0.85V or 6.25 Gb/s when V_{CCINT} = 0.72V.
4. For speed grades -1E and -1I, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s.
5. For speed grade -1LI, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s when V_{CCINT} = 0.85V or 5.15625 Gb/s when V_{CCINT} = 0.72V.
6. When the gearbox is used, these maximums refer to the XCLK. For more information, see the *Valid Data Width Combinations for TX Asynchronous Gearbox* table in the *UltraScale Architecture GTH Transceiver User Guide* (UG576).

Table 104: **GTH Transceiver Receiver Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$J_{T\_SJ2.5}$	Sinusoidal jitter (CPLL)(3)	2.5 Gb/s(5)	0.30	–	–	UI
$J_{T\_SJ1.25}$	Sinusoidal jitter (CPLL)(3)	1.25 Gb/s(6)	0.30	–	–	UI
J_{T_SJ500}	Sinusoidal jitter (CPLL)(3)	500 Mb/s(7)	0.30	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$J_{T\_TJSE3.2}$	Total jitter with stressed eye(8)	3.2 Gb/s	0.70	–	–	UI
$J_{T\_TJSE6.6}$		6.6 Gb/s	0.70	–	–	UI
$J_{T\_SJSE3.2}$	Sinusoidal jitter with stressed eye(8)	3.2 Gb/s	0.10	–	–	UI
$J_{T\_SJSE6.6}$		6.6 Gb/s	0.10	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of 10^{-12}.
3. The frequency of the injected sinusoidal jitter is 80 MHz.
4. CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
7. CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
8. Composite jitter with RX equalizer enabled. DFE disabled.

GTH Transceiver Electrical Compliance

The *UltraScale Architecture GTH Transceiver User Guide* (UG576) contains recommended use modes that ensure compliance for the protocols listed in Table 105. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 115: **GTY Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTYTX}	Serial data rate range		0.500	–	F_{GTYMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	21	–	ps
T_{FTX}	TX fall time	80%–20%	–	21	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500.00	ps
$T_{J32.75}$	Total jitter(2)(4)	32.75 Gb/s	–	–	0.35	UI
$D_{J32.75}$	Deterministic jitter(2)(4)		–	–	0.19	UI
$T_{J28.21}$	Total jitter(2)(4)	28.21 Gb/s	–	–	0.28	UI
$D_{J28.21}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J16.375}$	Total jitter(2)(4)	16.375 Gb/s	–	–	0.28	UI
$D_{J16.375}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J15.0}$	Total jitter(2)(4)	15.0 Gb/s	–	–	0.28	UI
$D_{J15.0}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.1 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.025 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J13.1}$	Total jitter(2)(4)	13.1 Gb/s	–	–	0.28	UI
$D_{J13.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_QPLL}$	Total jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$D_{J12.5\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_CPLL}$	Total jitter(3)(4)	12.5 Gb/s	–	–	0.33	UI
$D_{J12.5\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J11.3\_QPLL}$	Total jitter(2)(4)	11.3 Gb/s	–	–	0.28	UI
$D_{J11.3\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_QPLL}$	Total jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$D_{J10.3125\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_CPLL}$	Total jitter(3)(4)	10.3125 Gb/s	–	–	0.33	UI
$D_{J10.3125\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J9.953\_QPLL}$	Total jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$D_{J9.953\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J9.953\_CPLL}$	Total jitter(3)(4)	9.953 Gb/s	–	–	0.33	UI
$D_{J9.953\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J8.0}$	Total jitter(3)(4)	8.0 Gb/s	–	–	0.32	UI
$D_{J8.0}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J6.6}$	Total jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$D_{J6.6}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J5.0}$	Total jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$D_{J5.0}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.25}$	Total jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$D_{J4.25}$	Deterministic jitter(3)(4)		–	–	0.15	UI